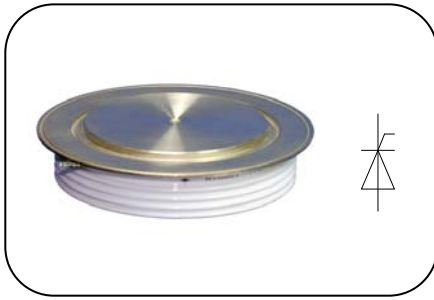


**Features**

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

**Typical Applications**

- Inductive heating
- Electronic welders
- Self-commutated inverters

**Part No. Y100KKG-KT100cT**

|                    |                |       |             |
|--------------------|----------------|-------|-------------|
| $I_{T(AV)}$        | 4890A          |       |             |
| $V_{DRM}, V_{RRM}$ | 2000V          | 2200V | 2500V 2800V |
|                    | 3000V          |       |             |
| $t_q$              | 40~130 $\mu$ s |       |             |

| SYMBOL                 | CHARACTERISTIC                                                       | TEST CONDITIONS                                                                               | $T_J(^{\circ}C)$ | VALUE |      |        | UNIT              |
|------------------------|----------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|------------------|-------|------|--------|-------------------|
|                        |                                                                      |                                                                                               |                  | Min   | Type | Max    |                   |
| $I_{T(AV)}$            | Mean on-state current                                                | 180° half sine wave 50Hz<br>Double side cooled,<br>$T_C=55^{\circ}C$                          | 125              |       |      | 4890   | A                 |
| $V_{DRM}$<br>$V_{RRM}$ | Repetitive peak off-state voltage<br>Repetitive peak reverse voltage | $t_p=10ms$                                                                                    | 125              | 1900  |      | 3000   | V                 |
| $I_{DRM}$<br>$I_{RRM}$ | Repetitive peak current                                              | at $V_{DRM}$<br>at $V_{RRM}$                                                                  | 125              |       |      | 250    | mA                |
| $I_{TSM}$              | Surge on-state current                                               | 10ms half sine wave                                                                           | 125              |       |      | 62     | kA                |
| $I^2t$                 | $I^2t$ for fusing coordination                                       | $V_R=0.6V_{RRM}$                                                                              |                  |       |      | 19220  | $A^2s \cdot 10^3$ |
| $V_{TO}$               | Threshold voltage                                                    |                                                                                               | 125              |       |      | 1.30   | V                 |
| $r_T$                  | On-state slope resistance                                            |                                                                                               |                  |       |      | 0.28   | m $\Omega$        |
| $V_{TM}$               | Peak on-state voltage                                                | $I_{TM}=5000A, F=90kN$                                                                        | 25               |       |      | 2.90   | V                 |
| dv/dt                  | Critical rate of rise of off-state voltage                           | $V_{DM}=0.67V_{DRM}$                                                                          | 125              |       |      | 1000   | V/ $\mu$ s        |
| di/dt                  | Critical rate of rise of on-state current                            | $V_{DM}=67\%V_{DRM}$ to 4000A<br>Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=1.5A$<br>Single pulse | 125              |       |      | 1200   | A/ $\mu$ s        |
| $Q_{rr}$               | Recovery charge                                                      | $I_{TM}=2000A, t_p=4000\mu s,$<br>$di/dt=-20A/\mu s, V_R=100V$                                | 125              |       | 2400 |        | $\mu C$           |
| $t_q$                  | Circuit commutated turn-off time                                     | $I_{TM}=2000A, t_p=4000\mu s, V_R=100V$<br>$dv/dt=30V/\mu s, di/dt=-20A/\mu s$                | 125              | 40    |      | 130    | $\mu s$           |
| $I_{GT}$               | Gate trigger current                                                 | $V_A=12V, I_A=1A$                                                                             | 25               | 40    |      | 450    | mA                |
| $V_{GT}$               | Gate trigger voltage                                                 |                                                                                               |                  | 0.9   |      | 4.5    | V                 |
| $I_H$                  | Holding current                                                      |                                                                                               |                  | 20    |      | 1000   | mA                |
| $I_L$                  | Latching current                                                     |                                                                                               |                  |       |      | 1000   | mA                |
| $V_{GD}$               | Non-trigger gate voltage                                             | $V_{DM}=67\%V_{DRM}$                                                                          | 125              |       |      | 0.3    | V                 |
| $R_{th(j-c)}$          | Thermal resistance<br>Junction to case                               | At 180° sine double side cooled<br>Clamping force 90kN                                        |                  |       |      | 0.005  | $^{\circ}C/W$     |
| $R_{th(c-h)}$          | Thermal resistance<br>case to heat sink                              |                                                                                               |                  |       |      | 0.0015 |                   |
| $F_m$                  | Mounting force                                                       |                                                                                               |                  | 81    |      | 108    | kN                |
| $T_{vj}$               | Junction temperature                                                 |                                                                                               |                  | -40   |      | 125    | $^{\circ}C$       |
| $T_{stg}$              | Stored temperature                                                   |                                                                                               |                  | -40   |      | 140    | $^{\circ}C$       |
| $W_t$                  | Weight                                                               |                                                                                               |                  |       | 2000 |        | g                 |
| Outline                | KT100cT                                                              |                                                                                               |                  |       |      |        |                   |

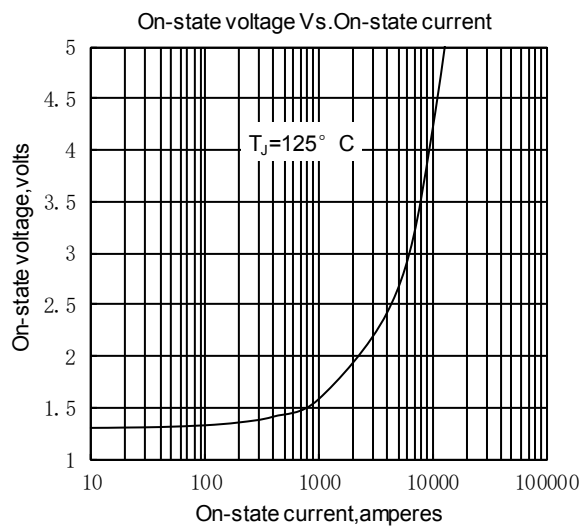


Fig.1

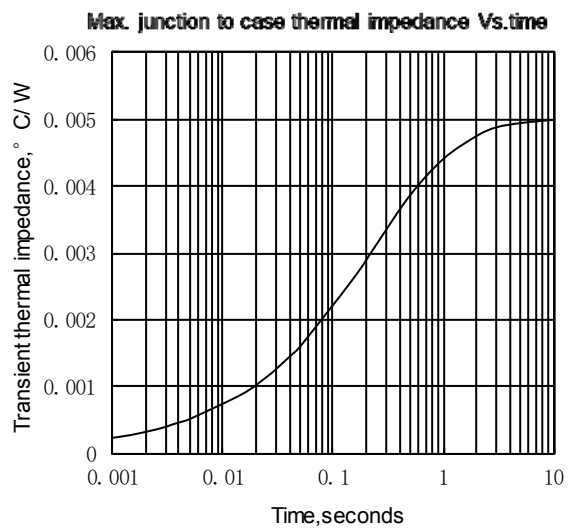


Fig.2

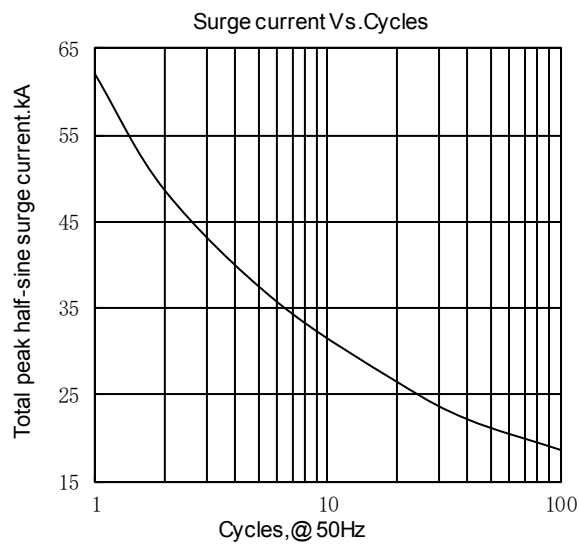


Fig.3

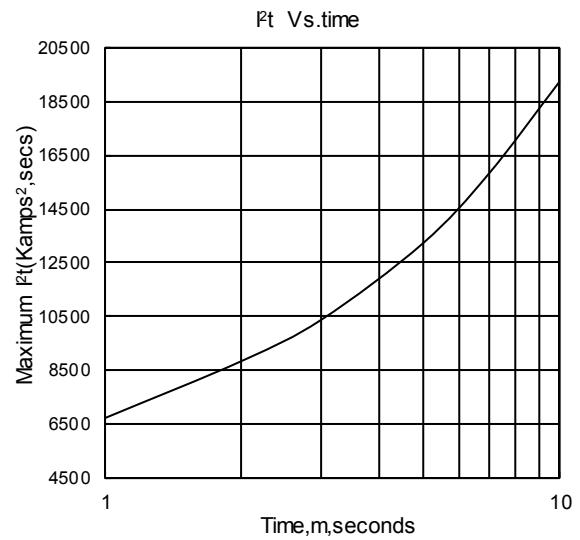


Fig.4

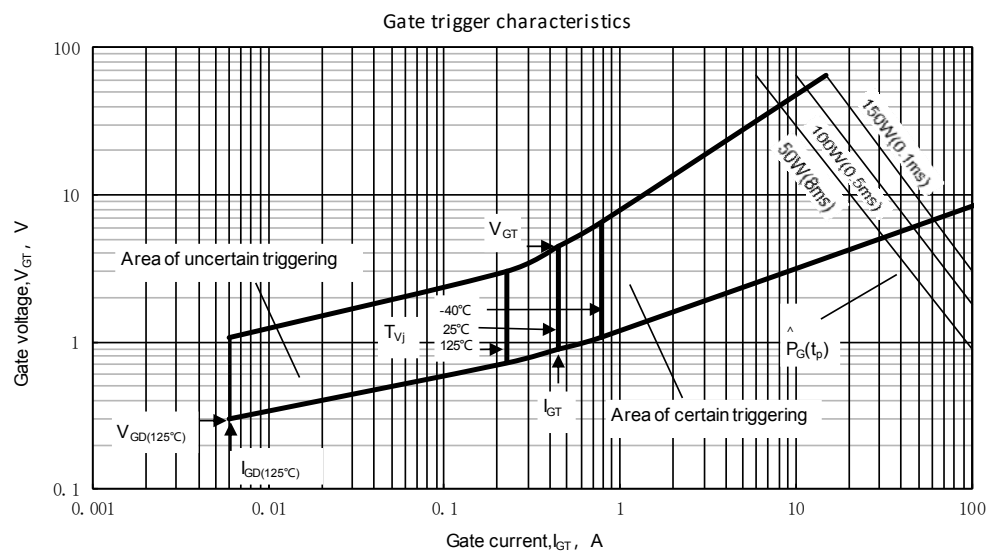
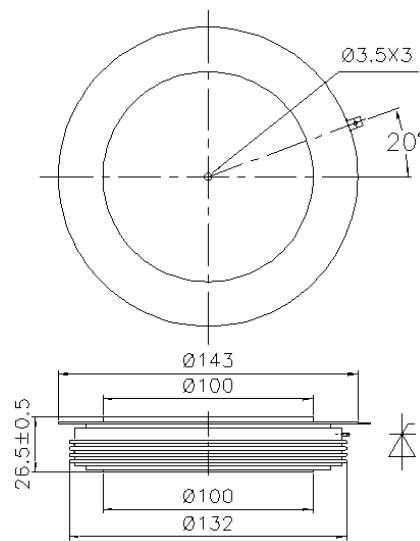


Fig.5

Outline:



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